

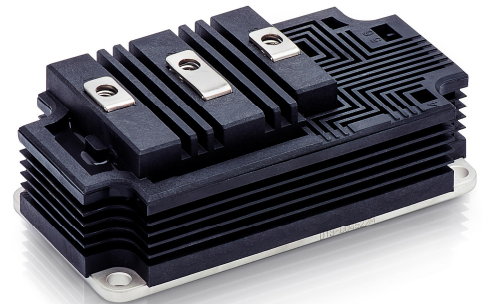
5SLG 0500P330300

HiPak DIODE Module

$$V_{RRM} = 3300 \text{ V}$$

$$I_F = 2 \times 500 \text{ A}$$

Ultra low-loss, rugged SPT+ diode
 Smooth switching SPT+ diode for good EMC
 AISiC base-plate for high power cycling capability
 AlN substrate for low thermal resistance
 2 diodes in 1 package
 Recognized under UL1557, File E196689



Maximum rated values ¹⁾

Parameter	Symbol	Conditions	min	max	Unit
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} \geq 25 \text{ }^\circ\text{C}$		3300	V
DC forward current	I_F			500	A
Peak forward current	I_{FRM}	$t_p = 1 \text{ ms, per Diode}$		1000	A
Total power dissipation	P_{tot}	$T_C = 25 \text{ }^\circ\text{C, } T_{vj} = 150 \text{ }^\circ\text{C, per Diode}$		2450	W
Surge current	I_{FSM}	$V_R = 0 \text{ V, } T_{vj} = 150 \text{ }^\circ\text{C, } t_p = 10 \text{ ms, half-sine wave, per Diode}$		4500	A
Isolation voltage	V_{isol}	1 min, $f = 50 \text{ Hz}$		6000	V
Junction temperature	T_{vj}			175	$^\circ\text{C}$
Junction operating temperature	$T_{vj(op)}$		-50	150	$^\circ\text{C}$
Case temperature	T_C		-50	125	$^\circ\text{C}$
Storage temperature	T_{stg}		-50	125	$^\circ\text{C}$
Mounting torques ²⁾	M_s	Base-heatsink, M6 screws	4	6	Nm
	M_{t1}	Main terminals, M6 screws	4	6	

¹⁾ Maximum rated values indicate limits beyond which damage to the device may occur per IEC 60747

²⁾ For detailed mounting instructions refer to Document No. 5SYA 2039

Diode characteristic values ³⁾

Parameter	Symbol	Conditions	min	typ	max	Unit
Forward voltage ⁴⁾	V_F	$I_F = 500 \text{ A}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	2.05	2.5	V
			$T_{vj} = 125 \text{ }^\circ\text{C}$	2.25	2.6	V
			$T_{vj} = 150 \text{ }^\circ\text{C}$	2.20		V
Continuous reverse current	I_R	$V_R = 3300 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		0.25	mA
			$T_{vj} = 125 \text{ }^\circ\text{C}$	3	6	mA
			$T_{vj} = 150 \text{ }^\circ\text{C}$	15		mA
Peak reverse recovery current	I_{RM}		$T_{vj} = 25 \text{ }^\circ\text{C}$	505		A
			$T_{vj} = 125 \text{ }^\circ\text{C}$	590		A
			$T_{vj} = 150 \text{ }^\circ\text{C}$	615		A
Recovered charge	Q_r	$V_{CC} = 1800 \text{ V}$, $I_F = 500 \text{ A}$, $di/dt = 2.1 \text{ kA}/\mu\text{s}$ $L_\sigma = 200 \text{ nH}$, inductive load Per Diode	$T_{vj} = 25 \text{ }^\circ\text{C}$	315		μC
			$T_{vj} = 125 \text{ }^\circ\text{C}$	510		μC
			$T_{vj} = 150 \text{ }^\circ\text{C}$	590		μC
Reverse recovery time	t_{rr}		$T_{vj} = 25 \text{ }^\circ\text{C}$	1125		ns
			$T_{vj} = 125 \text{ }^\circ\text{C}$	1440		ns
			$T_{vj} = 150 \text{ }^\circ\text{C}$	1630		ns
Reverse recovery energy	E_{rec}		$T_{vj} = 25 \text{ }^\circ\text{C}$	350		mJ
			$T_{vj} = 125 \text{ }^\circ\text{C}$	605		mJ
			$T_{vj} = 150 \text{ }^\circ\text{C}$	710		mJ

³⁾ Characteristic values according to IEC 60747 - 2

⁴⁾ Forward voltage is given at chip level

Package properties ⁵⁾

Parameter	Symbol	Conditions	min	typ	max	Unit
Diode thermal resistance junction to case	$R_{th(j-c)DIODE}$	Per Diode			0.050	K/W
Diode thermal resistance ²⁾ case to heatsink	$R_{th(c-s)DIODE}$	Per Diode, λ grease = 1W/m x K		0.048		K/W
Comparative tracking index	CTI			> 600		
Module stray inductance	$L_{\sigma AC}$	between C1 - A2		125		nH
Resistance, terminal-chip	$R_{AA'+CC'}$	Per Diode	$T_c = 25 \text{ }^\circ\text{C}$	0.25		m Ω
			$T_c = 125 \text{ }^\circ\text{C}$	0.33		
			$T_c = 150 \text{ }^\circ\text{C}$	0.35		

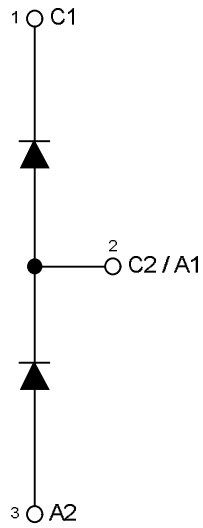
²⁾ For detailed mounting instructions refer to ABB Document No. 5SYA 2039

Mechanical properties ⁵⁾

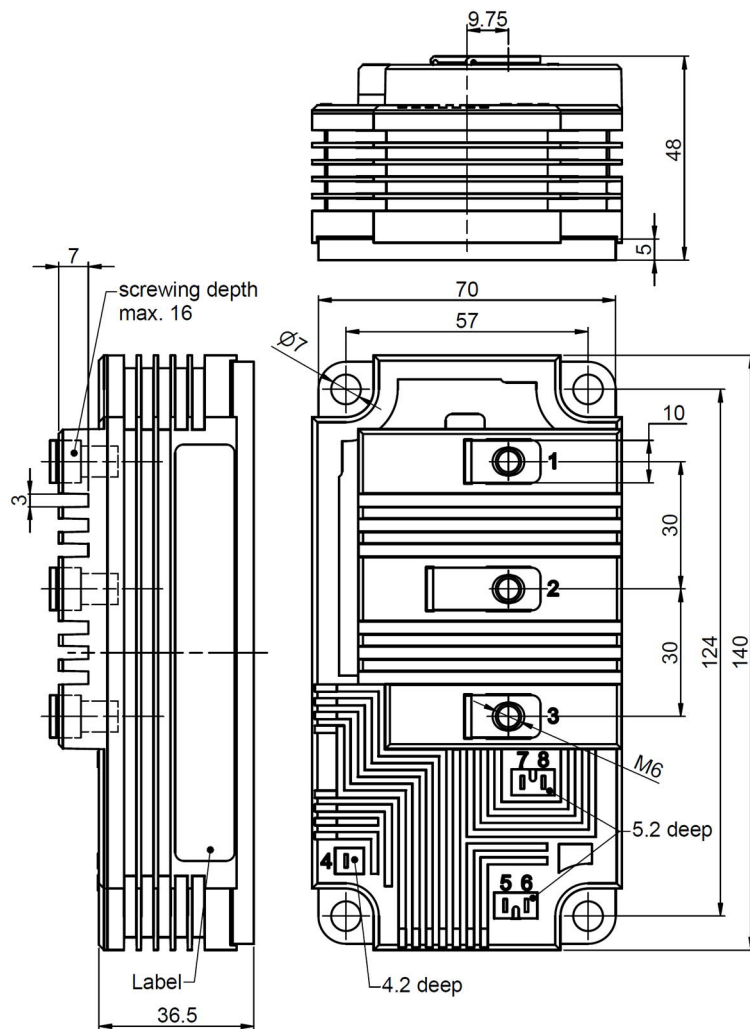
Parameter	Symbol	Conditions	min	typ	max	Unit
Dimensions	L x W x H	Typical		73 x 140 x 38		mm
Clearance distance in air	d_a	according to IEC 60664-1 and EN 50124-1	Term. to base:	35		mm
			Term. to term:	19		
Surface creepage distance	d_s	according to IEC 60664-1 and EN 50124-1	Term. to base:	64		mm
			A1 to C1:	54		
			A2 to C2:	78		
Mass	m			610		g

⁵⁾ Package and mechanical properties according to IEC 60747 - 15

Electrical configuration



Outline drawing ²⁾



Note: all dimensions are shown in millimeters

²⁾ For detailed mounting instructions refer to Document No. 5SYA 2039

This is an electrostatic sensitive device, please observe the international standard IEC 60747-1, chap. IX.
This product has been designed and qualified for Industrial Level.

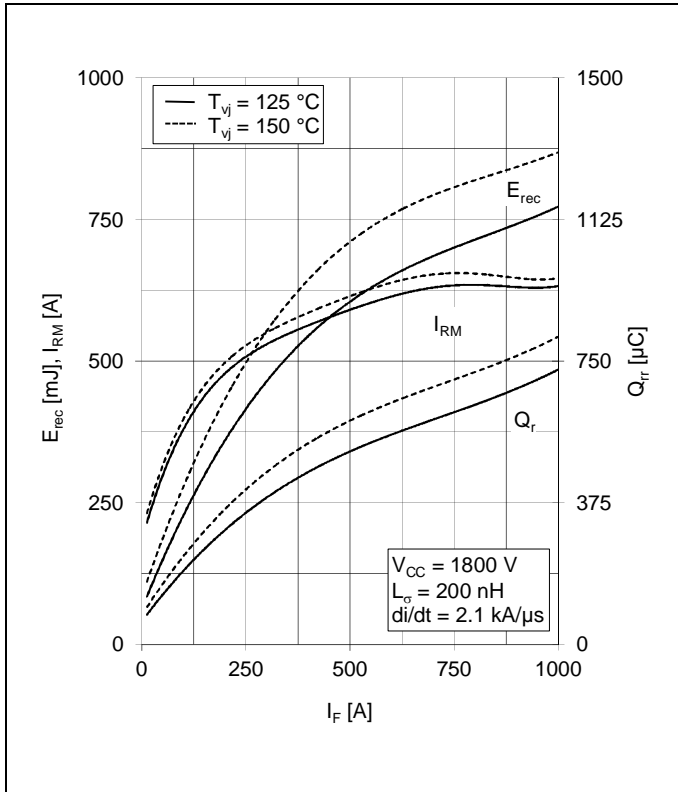


Fig. 1 Typical reverse recovery characteristics vs. forward current

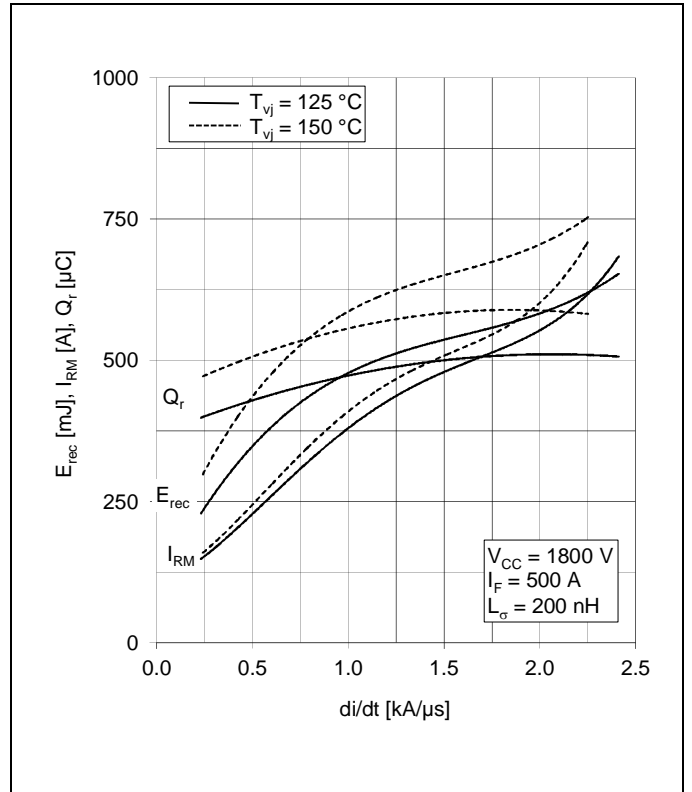


Fig. 2 Typical reverse recovery characteristics vs. di/dt

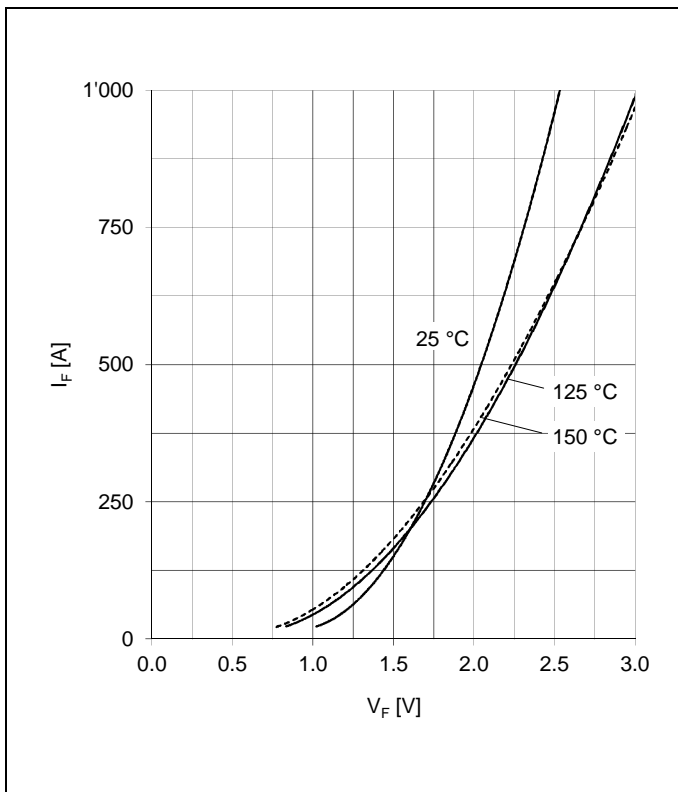


Fig. 3 Typical diode forward characteristics chip level

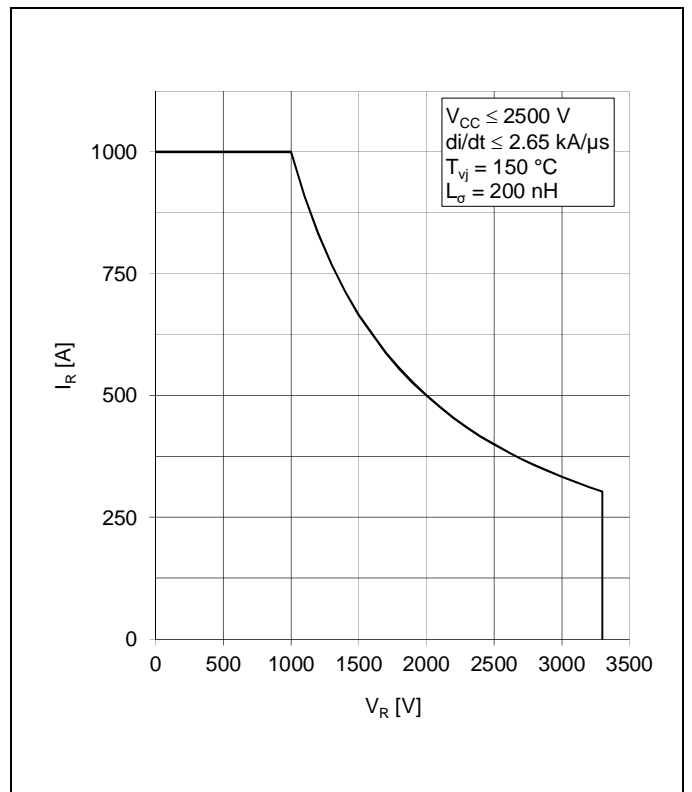


Fig. 4 Safe operating area diode (SOA)

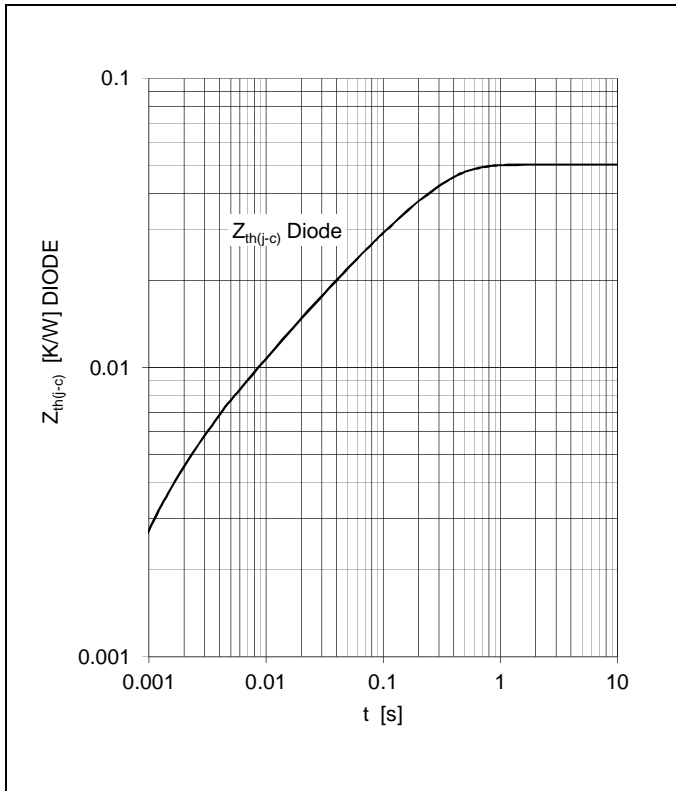


Fig. 5 Thermal impedance vs. time

Analytical function for transient thermal impedance:

$$Z_{th(j-c)}(t) = \sum_{i=1}^n R_i (1 - e^{-t/\tau_i})$$

DIODE	R _i (K/kW)	34.2	8.55	3.85	3.84	
	τ _i (ms)	203.6	30.1	7.53	1.57	

Related documents:

- 5SYA 2042 Failure rates of HiPak modules due to cosmic rays
- 5SYA 2043 Load - cycle capability of HiPaks
- 5SYA 2045 Thermal runaway during blocking
- 5SYA 2053 Applying IGBT
- 5SYA 2058 Surge currents for IGBT diodes
- 5SYA 2093 Thermal design of IGBT modules
- 5SYA 2098 Paralleling of IGBT modules
- 5SZK 9111 Specification of environmental class for HiPak Storage
- 5SZK 9112 Specification of environmental class for HiPak Transportation
- 5SZK 9113 Specification of environmental class for HiPak Operation (Industry)
- 5SZK 9120 Specification of environmental class for HiPak

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